

#### REMARKS

Favorable reconsideration of this application as amended is respectfully requested.

As a preliminary matter, it is noted that item (12) in the Office Action Summary refers to application number 10/343,701. Presumably, the intent was to indicate that the priority document has been received from the International Bureau. Appropriate correction is respectfully requested.

The title of the invention has been corrected by using the title suggested by the Examiner.

Appropriate corrections have been made in the specification to overcome the objection to the disclosure.

Elected Claims 44-57 have been cancelled in favor of new Claims 58-67, which more clearly distinguish Applicants' invention from the prior art.

New independent Claim 58 recites, *inter alia*, and that there is no exposure of the plurality of terminals and terminal leads from edges of the sealing member and that the metal layer over part of each of the plurality of terminals is formed by a printing process. Neither of these features is disclosed in the principal reference, Li et al. (U.S. Patent No. 6,348,729), relied upon in the rejection under 35 U.S.C. § 102(b). The secondary references relied upon in

the rejections under 35 U.S.C. 103(a) do not compensate for the deficiencies of Li et al.

As shown in Fig. 11 of Li et al., for example, the lower surface of the lead frame and the backside surface of the die are exposed through the plastic package body, and leads 222 are exposed from edges of the plastic package body. Therefore, if a semiconductor device constructed like this is mounted on a packaging substrate in proximity to another electronic part, such as another semiconductor device, a short circuit can occur.

Furthermore, Li et al. do not teach or suggest forming a metal layer over part of each of a plurality of terminals by a printing process.

A primary object of the present invention is to provide a semiconductor device which is thin. In the invention, a metal layer is formed by a printing process, that can control the stand-off height, compared, for example, with a ball electrode forming process. In the invention, the height of the semiconductor device can be kept to a value of not larger than 0.5mm, for example, even if the metal layer over the electrode terminals projects on the back surface of the sealing member. See, e.g., page 37, lines 1-16, and the paragraph bridging pages 41-42 of Applicants' specification.

Accordingly, the new claims distinguish patentably from the prior art and should be allowed.

This application is now in condition for allowance.

The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 (XA-10186) any fees under 37 C.F.R. §§ 1.16 and 1.17 that may be required by this paper and to credit any overpayment to that Account. If any extension of time is required in connection with the filing of this paper and has not been separately requested, such extension is hereby requested.

Respectfully submitted,

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